

Performance of Field-effect Transistors based on $\text{Nb}_x\text{W}_{1-x}\text{S}_2$ monolayer

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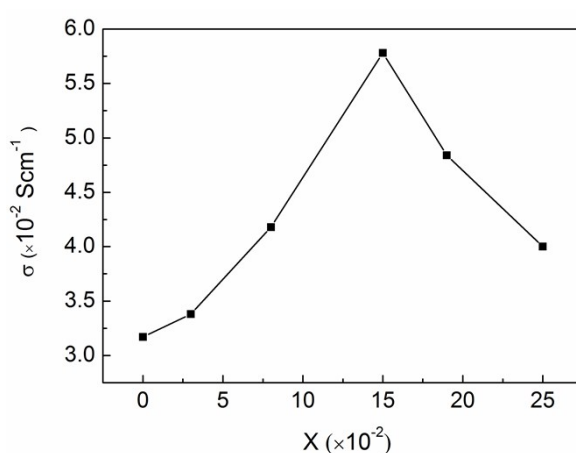


Figure S1. The electrical conductivities of $\text{Nb}_x\text{W}_{1-x}\text{S}_2$ film as a function of x .

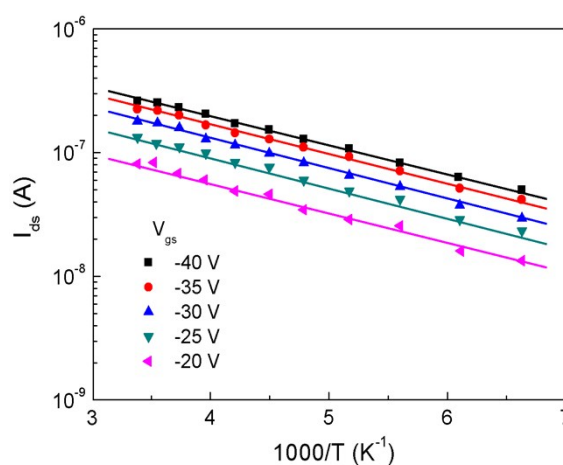


Figure S2. Arrhenius plot for barrier height extraction corresponding to Pd- $\text{Nb}_{0.15}\text{W}_{0.85}\text{S}_2$ contact